

## 1. General description

Planar passivated very sensitive gate Silicon Controlled Rectifier in a SOT54 (TO-92) plastic package.

## 2. Features and benefits

- Planar passivated for voltage ruggedness and reliability
- Very sensitive gate

## 3. Applications

- Ignition circuits
- Low power latching circuits
- Protection / shut-down circuits: lighting ballasts
- Protection / shut-down circuits: Switched Mode Power Supplies

## 4. Quick reference data

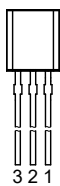

Table 1. Quick reference data

| Symbol                         | Parameter                            | Conditions  | Min | Typ | Max | Unit |
|--------------------------------|--------------------------------------|---|-----|-----|-----|------|
| $V_{RRM}$                      | repetitive peak reverse voltage      |   | -   | -   | 400 | V    |
| $I_{T(AV)}$                    | average on-state current             | half sine wave; $T_{lead} \leq 83\text{ °C}$ ; <a href="#">Fig. 1</a>   | -   | -   | 0.5 | A    |
| $I_{T(RMS)}$                   | RMS on-state current                 | half sine wave; $T_{lead} \leq 83\text{ °C}$ ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>  | -   | -   | 0.8 | A    |
| $I_{TSM}$                      | non-repetitive peak on-state current | half sine wave; $T_{j(init)} = 25\text{ °C}$ ; $t_p = 8.3\text{ ms}$  | -   | -   | 9   | A    |
|                                |                                      | half sine wave; $T_{j(init)} = 25\text{ °C}$ ; $t_p = 10\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>   | -   | -   | 8   | A    |
| $T_j$                          | junction temperature                 |   | -   | -   | 125 | °C   |
| <b>Static characteristics</b>  |                                      |   |     |     |     |      |
| $I_{GT}$                       | gate trigger current                 | $V_D = 12\text{ V}$ ; $I_T = 10\text{ mA}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 7</a>  | -   | -   | 50  | μA   |
| <b>Dynamic characteristics</b> |                                      |   |     |     |     |      |
| $dV_D/dt$                      | rate of rise of off-state voltage    | $V_{DM} = 268\text{ V}$ ; $T_j = 125\text{ °C}$ ; $R_{GK} = 1\text{ k}\Omega$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; <a href="#">Fig. 12</a> | 500 | 800 | -   | V/μs |

| Symbol | Parameter | Conditions   | Min | Typ | Max | Unit             |
|--------|-----------|--|-----|-----|-----|------------------|
|        |           | $V_{DM} = 268 \text{ V}$ ; $T_j = 125 \text{ }^\circ\text{C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit; <a href="#">Fig. 12</a> | -   | 25  | -   | V/ $\mu\text{s}$ |

## 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline   | Graphic symbol  |
|-----|--------|-------------|--|---|
| 1   | A      | anode       |  <p>TO-92 (SOT54)</p> |  |
| 2   | G      | gate        |  |   |
| 3   | K      | cathode     |  |   |

## 6. Ordering information

Table 3. Ordering information

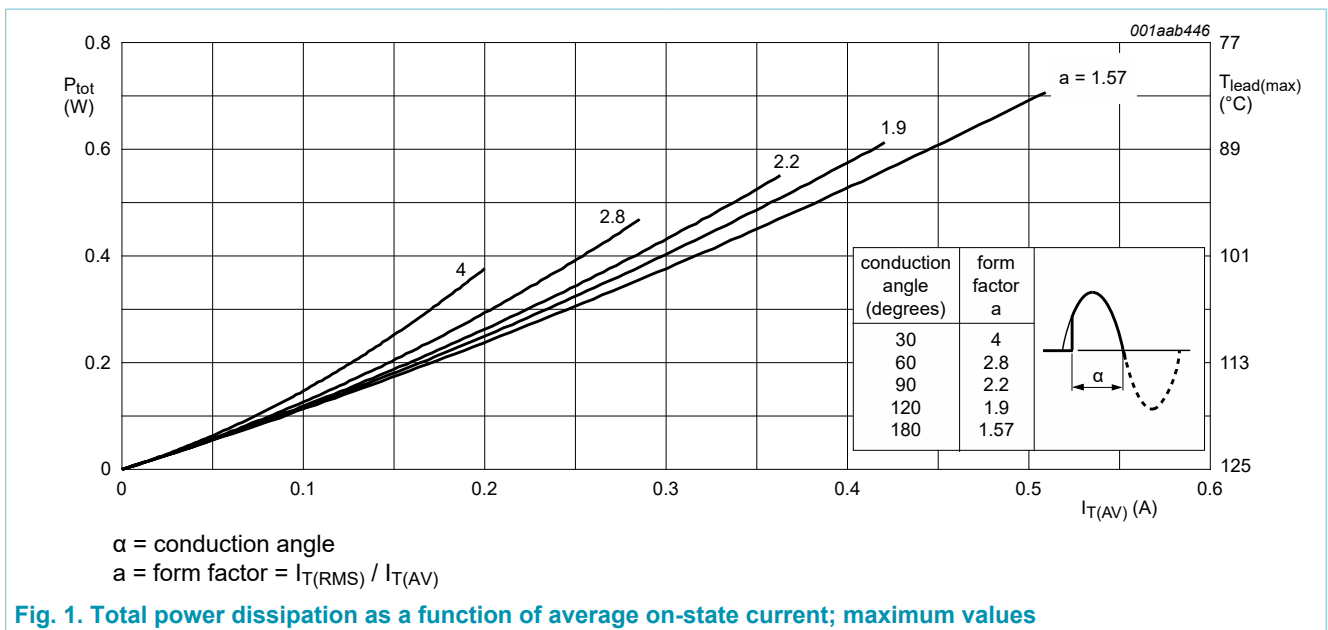
| Type number | Package |   |         |
|-------------|---------|---|---------|
|             | Name    | Description   | Version |
| BT169D-L    | TO-92   | plastic single-ended leaded (through hole) package; 3 leads | SOT54   |

## 7. Limiting values

**Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol       | Parameter                            | Conditions   | Min | Max  | Unit                   |
|--------------|--------------------------------------|--|-----|------|------------------------|
| $V_{DRM}$    | repetitive peak off-state voltage    |  | -   | 400  | V                      |
| $V_{RRM}$    | repetitive peak reverse voltage      |  | -   | 400  | V                      |
| $I_{T(AV)}$  | average on-state current             | half sine wave; $T_{lead} \leq 83\text{ }^{\circ}\text{C}$ ; Fig. 1                                | -   | 0.5  | A                      |
| $I_{T(RMS)}$ | RMS on-state current                 | half sine wave; $T_{lead} \leq 83\text{ }^{\circ}\text{C}$ ; Fig. 2; Fig. 3                        | -   | 0.8  | A                      |
| $I_{TSM}$    | non-repetitive peak on-state current | half sine wave; $T_{j(init)} = 25\text{ }^{\circ}\text{C}$ ; $t_p = 8.3\text{ ms}$                 | -   | 9    | A                      |
|              |                                      | half sine wave; $T_{j(init)} = 25\text{ }^{\circ}\text{C}$ ; $t_p = 10\text{ ms}$ ; Fig. 4; Fig. 5 | -   | 8    | A                      |
| $I^2t$       | $I^2t$ for fusing                    | $t_p = 10\text{ ms}$ ; SIN   | -   | 0.32 | $\text{A}^2\text{s}$   |
| $dl_T/dt$    | rate of rise of on-state current     | $I_T = 2\text{ A}$ ; $I_G = 10\text{ mA}$ ; $dl_G/dt = 100\text{ mA}/\mu\text{s}$                  | -   | 50   | $\text{A}/\mu\text{s}$ |
| $I_{GM}$     | peak gate current                    |  | -   | 1    | A                      |
| $V_{RGM}$    | peak reverse gate voltage            |  | -   | 5    | V                      |
| $P_{GM}$     | peak gate power                      |  | -   | 2    | W                      |
| $P_{G(AV)}$  | average gate power                   | over any 20 ms period  | -   | 0.1  | W                      |
| $T_{stg}$    | storage temperature                  |  | -40 | 150  | $^{\circ}\text{C}$     |
| $T_j$        | junction temperature                 |  | -   | 125  | $^{\circ}\text{C}$     |



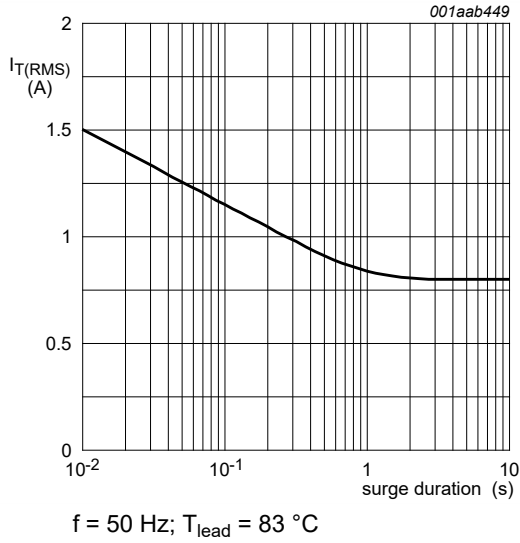


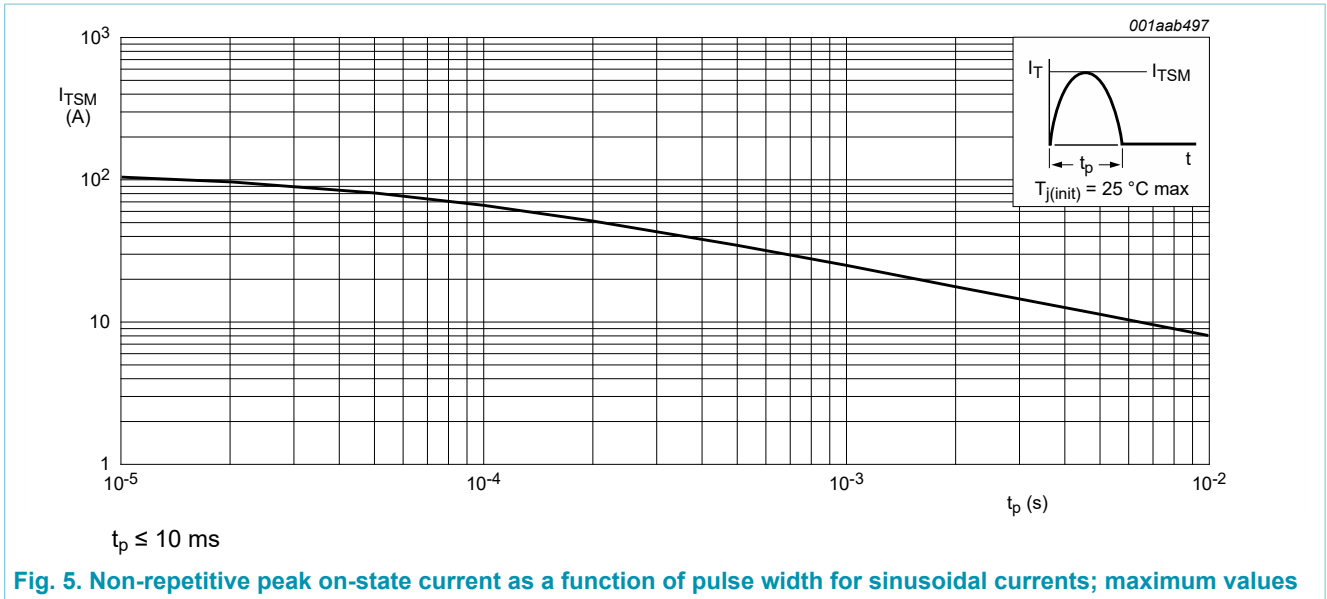
Fig. 2. RMS on-state current as a function of surge duration for sinusoidal currents



Fig. 3. RMS on-state current as a function of lead temperature; maximum values



Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



## 8. Thermal characteristics

Table 5. Thermal characteristics

| Symbol           | Parameter  | Conditions  | Min | Typ | Max | Unit |
|------------------|--|---|-----|-----|-----|------|
| $R_{th(j-lead)}$ | thermal resistance from junction to lead             | <a href="#">Fig. 6</a>                            | -   | -   | 60  | K/W  |
| $R_{th(j-a)}$    | thermal resistance from junction to ambient free air | printed circuit board mounted: lead length = 4 mm | -   | 150 | -   | K/W  |



Fig. 6. Transient thermal impedance from junction to lead as a function of pulse width

## 9. Characteristics

Table 6. Characteristics

| Symbol                         | Parameter                         | Conditions  | Min | Typ  | Max | Unit                   |
|--------------------------------|-----------------------------------|---|-----|------|-----|------------------------|
| <b>Static characteristics</b>  |                                   |   |     |      |     |                        |
| $I_{GT}$                       | gate trigger current              | $V_D = 12\text{ V}$ ; $I_T = 10\text{ mA}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a>  | -   | -    | 50  | $\mu\text{A}$          |
| $I_L$                          | latching current                  | $V_D = 12\text{ V}$ ; $I_G = 0.5\text{ mA}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 8</a>   | -   | 2    | 4   | mA                     |
| $I_H$                          | holding current                   | $V_D = 12\text{ V}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 9</a>   | -   | 0.4  | 1   | mA                     |
| $V_T$                          | on-state voltage                  | $I_T = 1.2\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 10</a>   | -   | 1.25 | 1.7 | V                      |
| $V_{GT}$                       | gate trigger voltage              | $V_D = 12\text{ V}$ ; $I_T = 10\text{ mA}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 11</a>   | -   | 0.5  | 0.8 | V                      |
|                                |                                   | $V_D = 12\text{ V}$ ; $I_T = 10\text{ mA}$ ; $T_j = 125\text{ }^\circ\text{C}$ ; <a href="#">Fig. 11</a>  | 0.2 | 0.3  | -   | V                      |
| $I_D$                          | off-state current                 | $V_D = 400\text{ V}$ ; $R_{GK(\text{ext})} = 1\text{ k}\Omega$ ; $T_j = 25\text{ }^\circ\text{C}$   | -   | -    | 2   | $\mu\text{A}$          |
|                                |                                   | $V_D = 400\text{ V}$ ; $R_{GK(\text{ext})} = 1\text{ k}\Omega$ ; $T_j = 125\text{ }^\circ\text{C}$  | -   | 0.05 | 0.1 | mA                     |
| $I_R$                          | reverse current                   | $V_R = 400\text{ V}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; $R_{GK(\text{ext})} = 1\text{ k}\Omega$   | -   | 0.05 | 2   | $\mu\text{A}$          |
|                                |                                   | $V_R = 400\text{ V}$ ; $T_j = 125\text{ }^\circ\text{C}$ ; $R_{GK(\text{ext})} = 1\text{ k}\Omega$  | -   | 0.05 | 0.1 | mA                     |
| <b>Dynamic characteristics</b> |                                   |   |     |      |     |                        |
| $dV_D/dt$                      | rate of rise of off-state voltage | $V_{DM} = 268\text{ V}$ ; $T_j = 125\text{ }^\circ\text{C}$ ; $R_{GK} = 1\text{ k}\Omega$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; <a href="#">Fig. 12</a> | 500 | 800  | -   | $\text{V}/\mu\text{s}$ |
|                                |                                   | $V_{DM} = 268\text{ V}$ ; $T_j = 125\text{ }^\circ\text{C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit; <a href="#">Fig. 12</a>            | -   | 25   | -   | $\text{V}/\mu\text{s}$ |

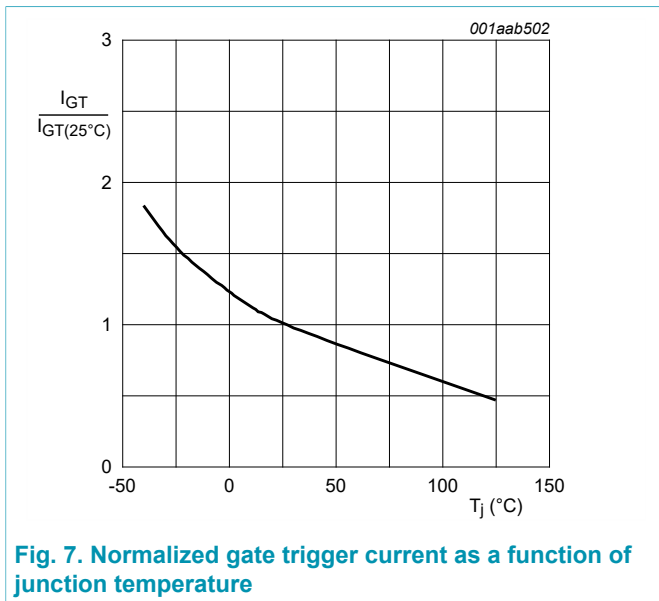


Fig. 7. Normalized gate trigger current as a function of junction temperature

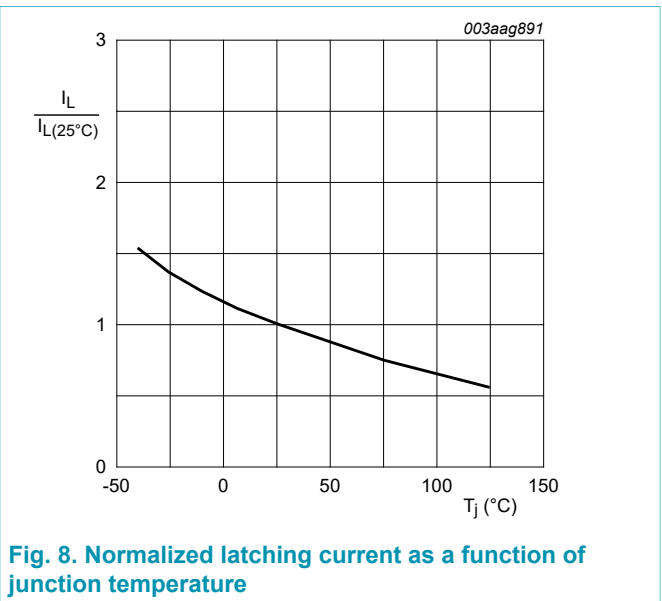


Fig. 8. Normalized latching current as a function of junction temperature

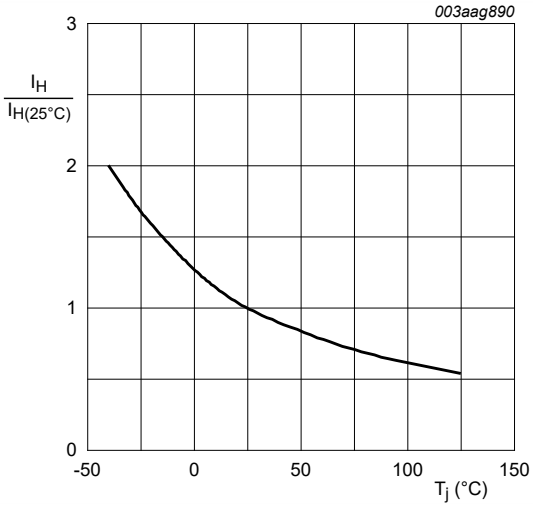
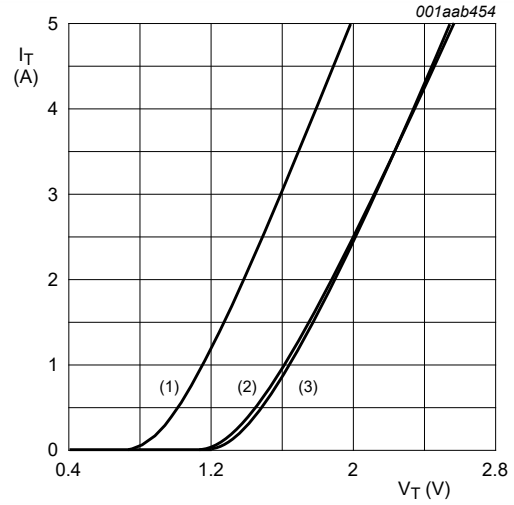


Fig. 9. Normalized holding current as a function of junction temperature



$V_o = 1.067 \text{ V}; R_s = 0.187 \Omega$

- (1)  $T_j = 125 \text{ }^\circ\text{C}$ ; typical values
- (2)  $T_j = 125 \text{ }^\circ\text{C}$ ; maximum values
- (3)  $T_j = 25 \text{ }^\circ\text{C}$ ; maximum values

Fig. 10. On-state current as a function of on-state voltage

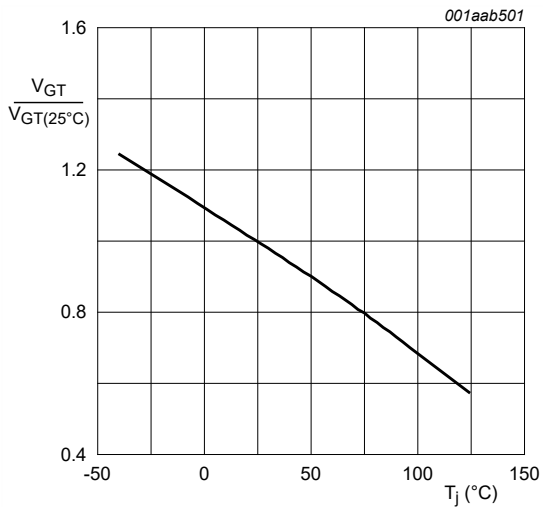
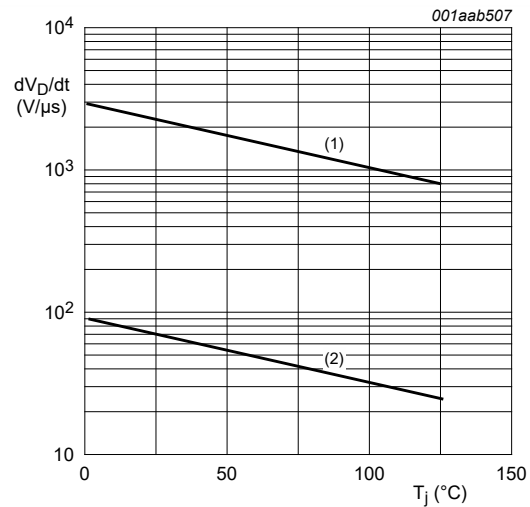


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

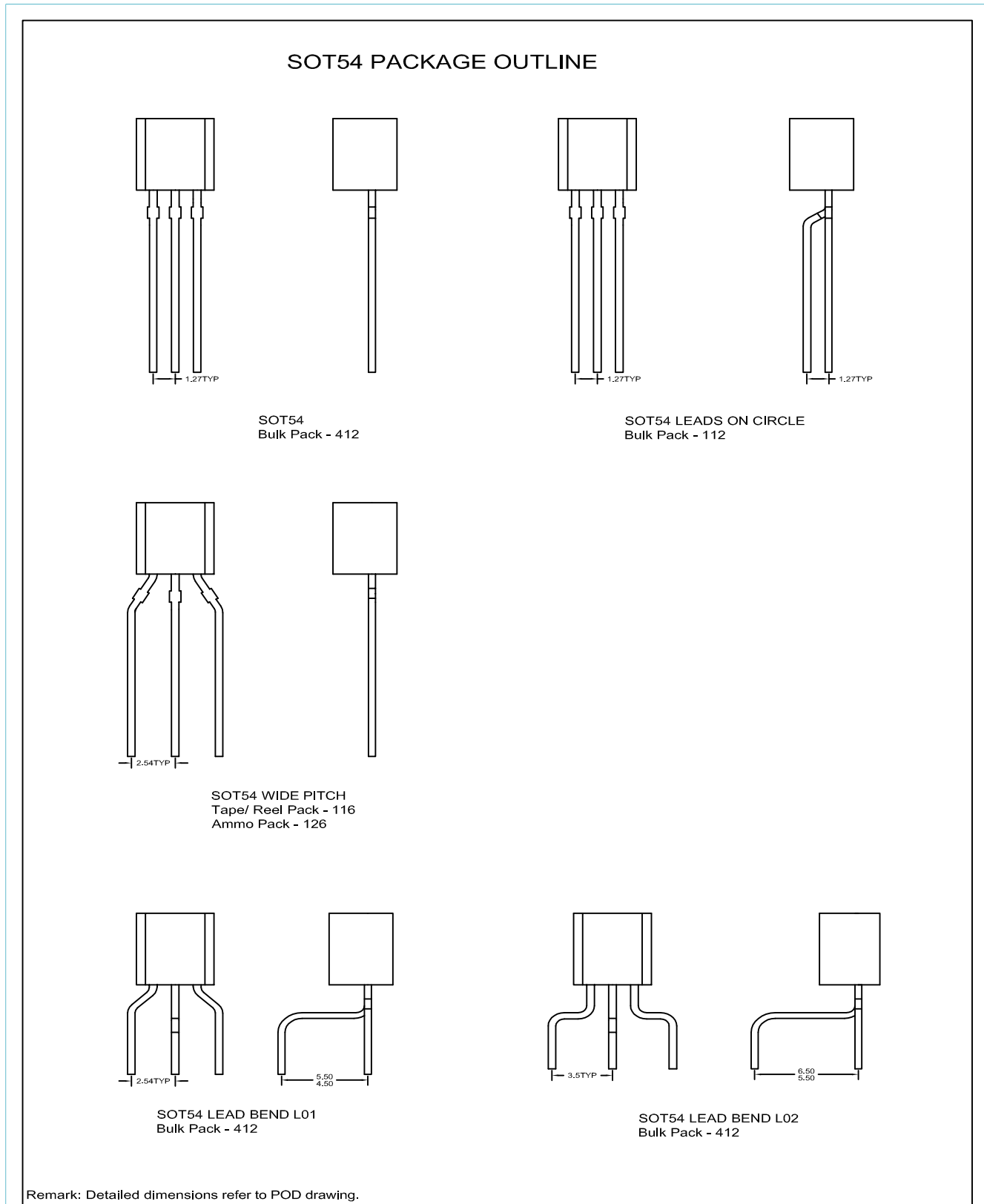


- (1)  $R_{GK} = 1 \text{ k}\Omega$
- (2) gate open circuit

Fig. 12. Critical rate of rise of off-state voltage as a function of junction temperature; typical values



### 10. Package outline



**Fig. 13. Package outline TO-92 (SOT54)**

## 11. Legal information

### Data sheet status

| Document status [1][2]         | Product status [3] | Definition  |
|--------------------------------|--------------------|---|
| Objective [short] data sheet   | Development        | This document contains data from the objective specification for product development. |
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- [1] Please consult the most recently issued document before initiating or completing a design.
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